



# EMIF02-600FU7

Application Specific Discretes  
A.S.D.™

10-BIT WIDE EMI FILTER  
INCLUDING ESD PROTECTION

## MAIN APPLICATIONS

Where EMI filtering in ESD sensitive equipment is required :

- Computers and printers
- Communication systems
- Mobile phones
- MCU Boards

## DESCRIPTION

The EMIF02-600FU7 is a highly integrated array designed to suppress EMI / RFI noise in all systems subjected to electromagnetic interferences.

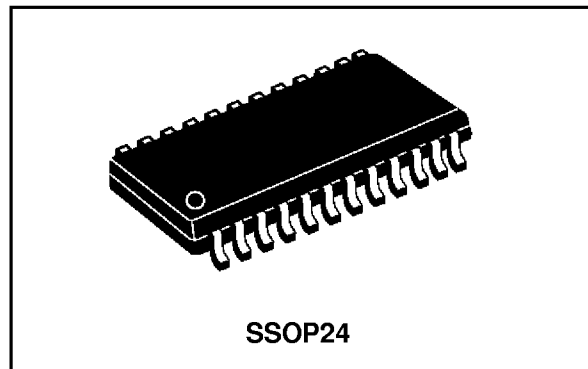
Additionally, this filter includes an ESD protection circuitry which prevents the protected device from destruction when subjected to ESD surges up to 15 kV. The EMIF02-600FU7 provides best efficiency when using separated inputs and outputs, in the so-called 4-points structure.

## BENEFITS

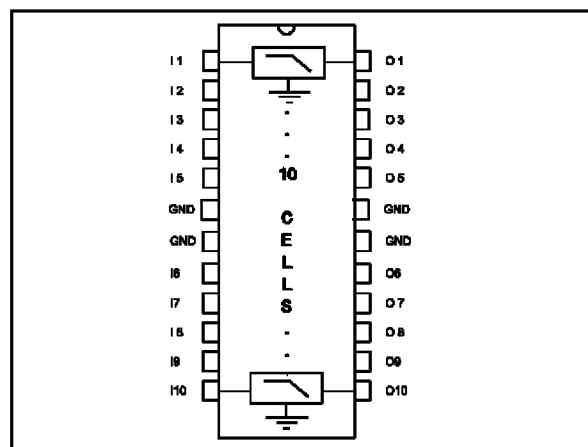
- 10-bit EMI bi-directional low-pass-filter
- Enhanced ESD protection for the protected device, optimized by the four point structure
- High flexibility in the design of high density boards

## COMPLIES WITH THE FOLLOWING STANDARDS :

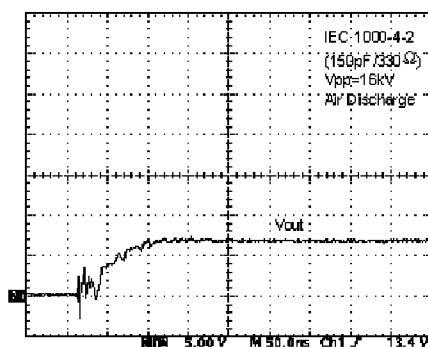
IEC 1000-4-2	15kV	(air discharge)
	8 kV	(contact discharge)



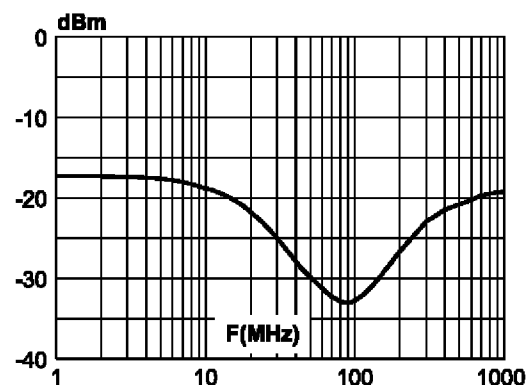
## FUNCTIONAL DIAGRAM



## ESD response to IEC1000-4-2 (15 kV air discharge)



## Filtering response (with 50Ω line)



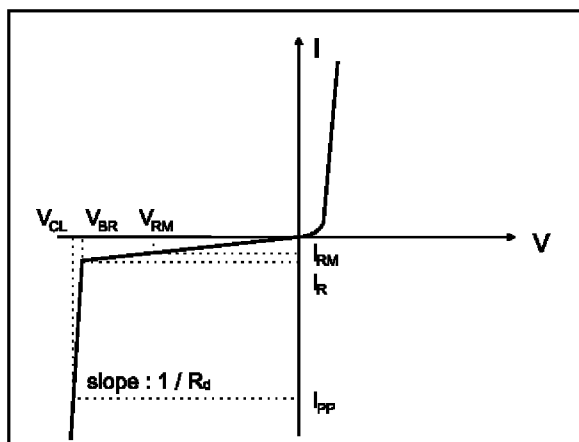
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**ABSOLUTE MAXIMUM RATINGS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ )

Symbol	Parameter and test conditions	Value	Unit
$V_{PP}$	ESD discharge IEC1000-4-2, air discharge ESD discharge IEC1000-4-2, contact discharge	16 9	kV
$T_j$	Junction temperature	150	$^{\circ}\text{C}$
$T_{op}$	Operating temperature range	-40 to + 85	$^{\circ}\text{C}$
$T_{stg}$	Storage temperature range	-55 to +150	$^{\circ}\text{C}$
$T_L$	Lead solder temperature (10 second duration)	260	$^{\circ}\text{C}$

**ELECTRICAL CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ )

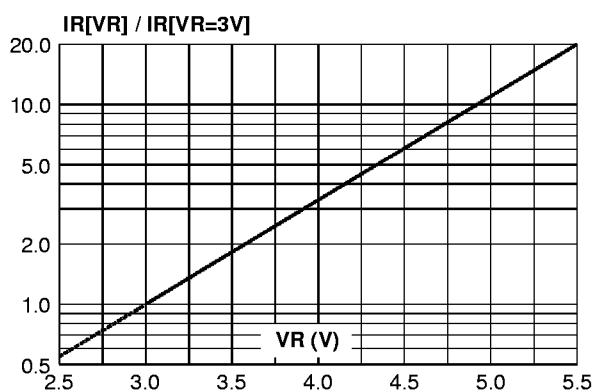
Symbol	Parameter
$V_{BR}$	Breakdown voltage
$I_{RM}$	Leakage current @ $V_{RM}$
$V_{RM}$	Stand-off voltage
$V_{CL}$	Clamping voltage
$R_d$	Dynamic impedance
$I_{PP}$	Peak pulse current
$R_{I/O}$	Serial resistance between Input and Output



Symbol	Test conditions	Min.	Typ.	Max.	Unit
$V_{BR}$	$I_R = 1\text{ mA}$	6	7	8	V
$I_{RM}$	$V_{RM} = 3\text{ V}$			1	$\mu\text{A}$
$R_{I/O}$	Serial resistance between Input and Output	480	600	720	$\Omega$
$R_d$	$I_{pp} = 10\text{ A}$ , $t_p = 2.5\text{ }\mu\text{s}$ (see note 1)		0.55		$\Omega$

Note 1 : to calculate the ESD residual voltage, please refer to the paragraph "ESD PROTECTION" on pages 4 & 5

**Fig.1** : Relative variation of leakage current versus reverse voltage(Typical values)



## TECHNICAL INFORMATION

### FREQUENCY BEHAVIOR

The EMIF02-600FU7 is firstly designed as an EMI/RFI filter. This low-pass filter is characterized by the following parameters:

- Cut-off frequency
- Insertion loss
- High frequency rejection

**Fig A1 :** EMIF02-600FU7 frequency response curve.

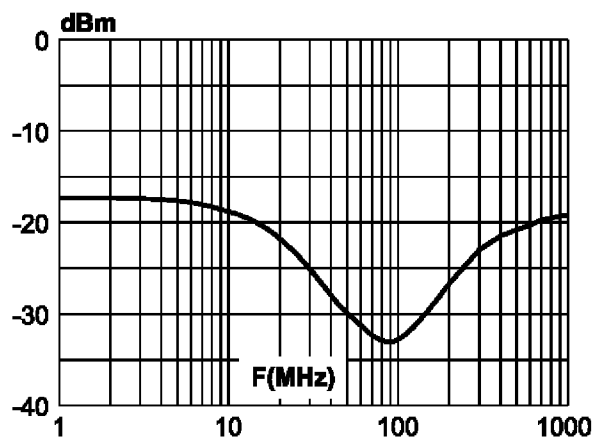
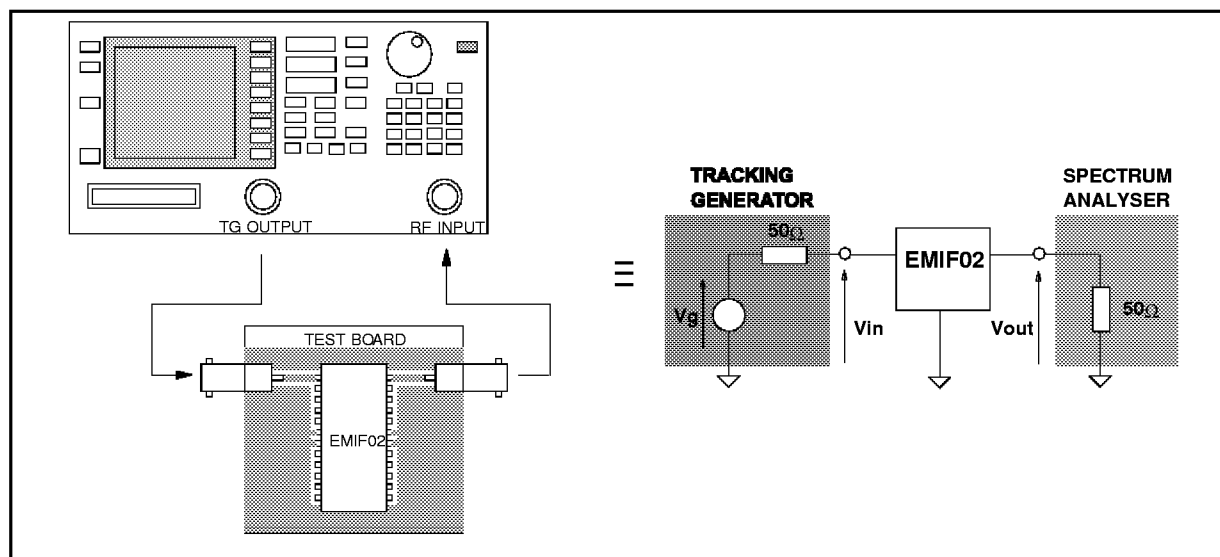


Figure A1 gives these parameters, in particular the signal rejection at the GSM frequency is about -20dBm at 900MHz, while the attenuation for FM broadcast range (around 100MHz) is better than -32dBm

**Fig A2 :** Measurement conditions



## EMIF02-600FU7

### ESD PROTECTION

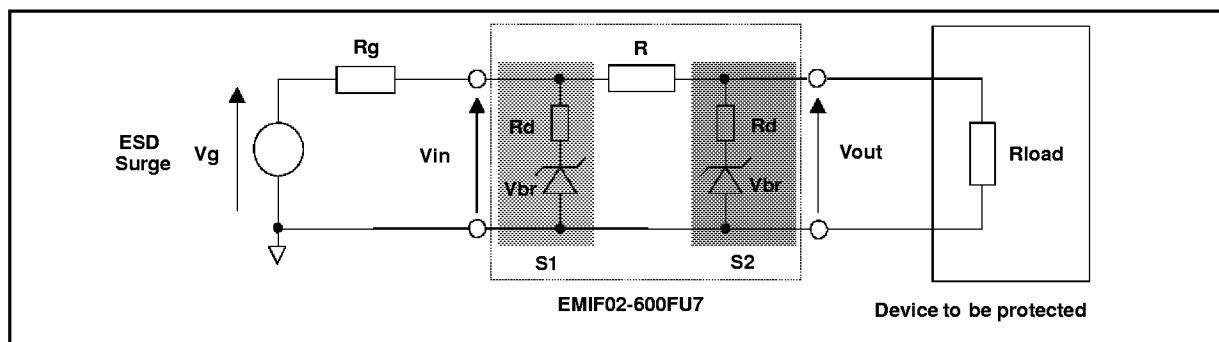
In addition to its filtering function, the EMIF02-600FU7 is particularly optimized to perform ESD protection.

ESD protection is based on voltage clamping which can be calculated by :

$$V_{CL} = V_{BR} + R_d \cdot I_{PP}$$

This protection function is splitted in 2 stages. As shown in figure A3, the ESD strikes are clamped by the first stage S1 and then its remaining overvoltage is applied to the second stage through the resistor R. Such a configuration makes the output voltage  $V_{out}$  very low.

**Fig A3 : ESD clamping behavior**



To have a good approximation of the remaining voltages at both  $V_{in}$  and  $V_{out}$  stages, we provide the typical dynamical resistance value  $R_d$ . By taking into account these following hypothesis :  $R \gg R_d$ ,  $R_g \gg R_d$  and  $R_{load} \gg R_d$ , it gives these formulas:

$$V_{in} = \frac{R_g \cdot V_{br} + R_d \cdot V_g}{R_g}$$

$$V_{out} = \frac{R \cdot V_{br} + R_d \cdot V_{in}}{R}$$

The results of the calculation done for  $V_g=8kV$ ,  $R_g=330\Omega$  (IEC1000-4-2 standard) and  $V_{BR}=7V$  (typ.) give:

$$V_{in} = 20.33 V$$

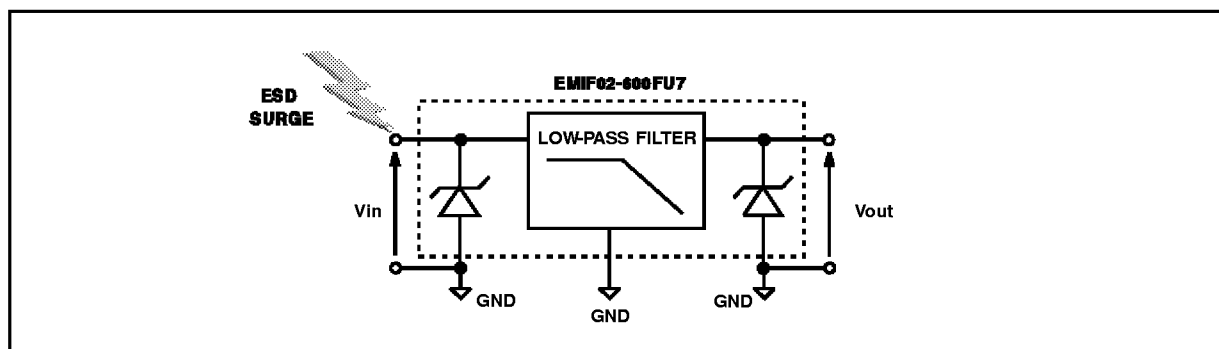
$$\underline{V_{out} = 7.01 V}$$

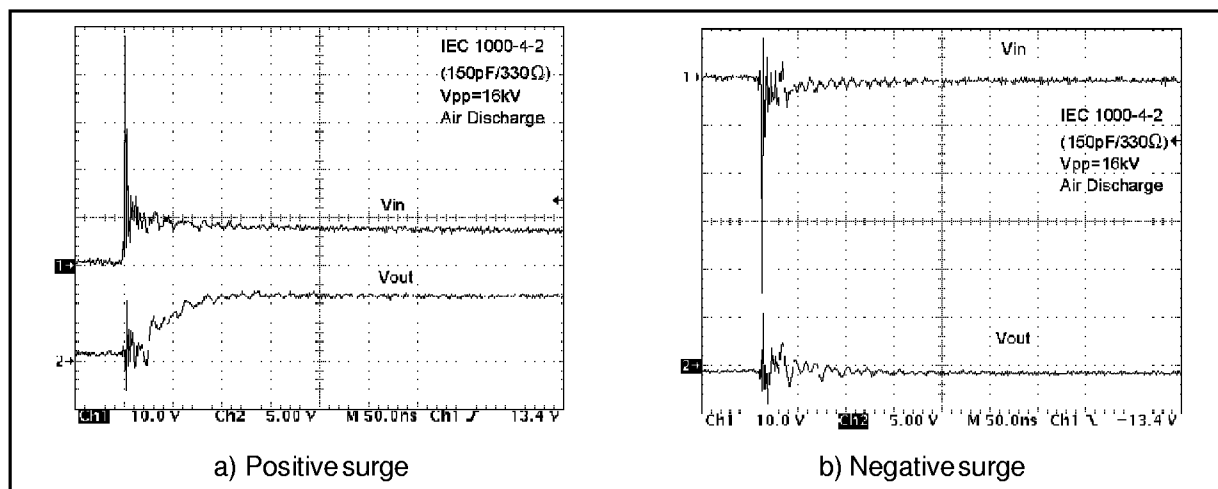
This confirms the very low remaining voltage across the device to be protected. It is also important to note that in this approximation the parasitic inductance effect was not taken into account. This could be few tenths of volts during few ns at the  $V_{in}$  side. This parasitic effect is not present at the  $V_{out}$  side due the low current involved after the resistance R.

The measurements shown here after illustrate very clearly (Fig. A5a) the high efficiency of the ESD protection :

- no influence of the parasitic inductances on  $V_{out}$  stage
- $V_{out}$  clamping voltage very close to  $V_{BR}$

**Fig A4 : Measurement conditions**

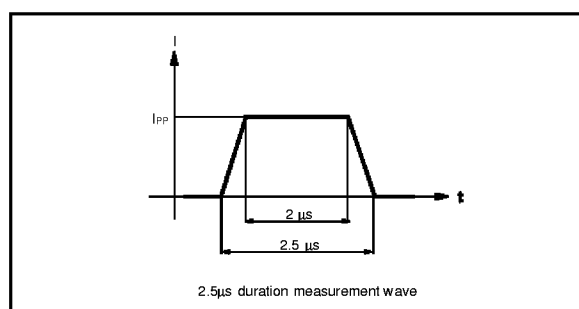


**Fig A5 :** Remaining voltage at both stages S1 (Vin) and S2 (Vout) during ESD surge

Please note that the EMIF02-600FU7 is not only acting for positive ESD surges but also for negative ones. For these kind of disturbances it clamps close to ground voltage as shown in Fig. A5b.

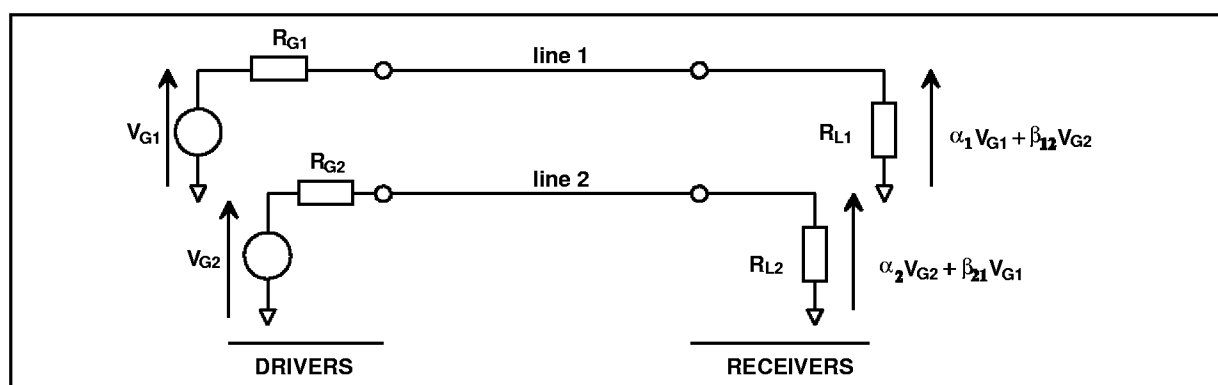
#### NOTE: DYNAMIC RESISTANCE MEASUREMENT

As the value of the dynamic resistance remains stable for a surge duration lower than 20 $\mu$ s, the 2.5 $\mu$ s rectangular surge is well adapted. In addition both rise and fall times are optimized to avoid any parasitic phenomenon during the measurement of Rd.

**Fig A6 :** Rd measurement current wave

### CROSSTALK BEHAVIOR

#### 1- Crosstalk phenomena

**Fig A7 :** Crosstalk phenomena

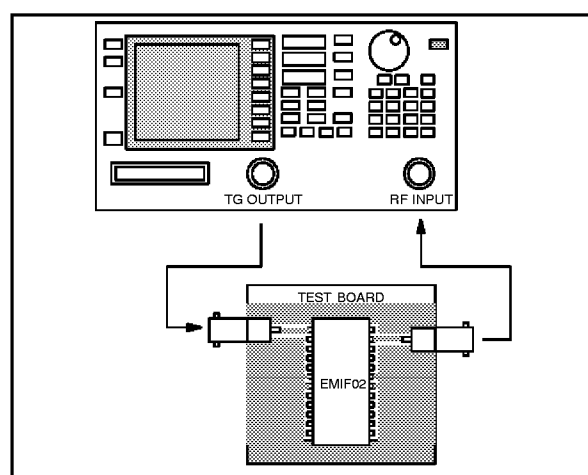
The crosstalk phenomena are due to the coupling between 2 lines. The coupling factor ( $\beta_{12}$  or  $\beta_{21}$ ) increases when the gap across lines decreases, particularly in silicon dice. In the example above the expected signal on load  $R_{L2}$  is  $\alpha_2 V_{G2}$ , in fact the real voltage at this point has got an extra value  $\beta_{21} V_{G1}$ . This part of the  $V_{G1}$  signal represents the effect of the crosstalk phenomenon of the line 1 on the line 2. This phenomenon has to be taken into account when the drivers impose fast digital data or high frequency analog signals in the disturbing line. The perturbed line will be more affected if it works with low voltage signal or high load impedance (few k $\Omega$ ). The following chapters give the value of both digital and analog crosstalk.

## 2- Digital Crosstalk

The diagram shows a 2T1D circuit. A 5KHz square pulse generator is connected to the inputs of two 74HC04 inverters. The outputs of these inverters are connected to the inputs of the EMIF02-600FU7 memory. The memory's outputs are connected to two more 74HC04 inverters, which produce the final square wave outputs. The circuit is powered by +5V and ground. Labels include 'Line 1', 'Line 2',  $V_{G1}$ , and  $\beta_{21} V_{G1}$ .

Figure A9 shows that in such a condition signal from 0 to 5V and rise time of 10 ns, the impact on the disturbed line is less than 20mV peak to peak. No data disturbance was noted on the concerned line. The same results were obtained with falling edges.

**Fig A10 : Analog crosstalk measurement**



6/9

## PSpice MODEL

**Fig A12 :** PSpice model of one EMIF02-600FU7 cell

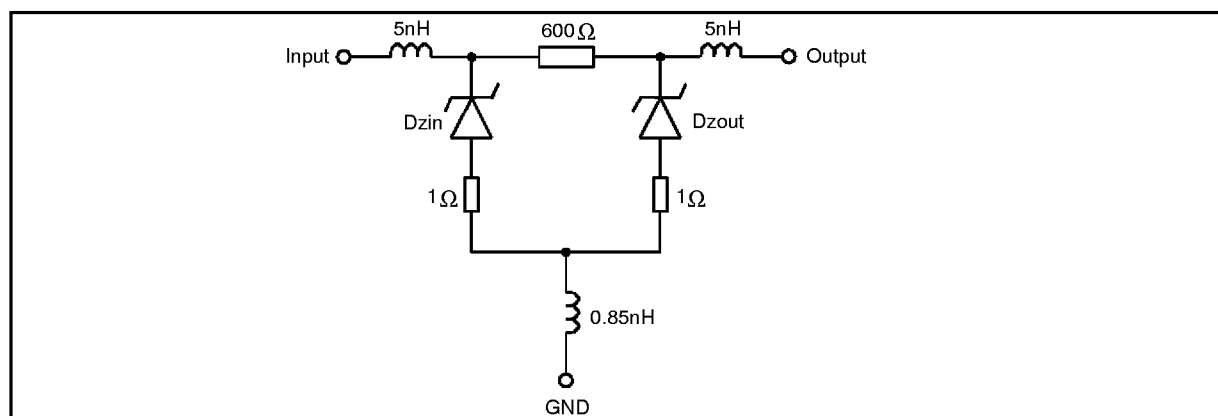


Figure A12 shows the PSpice model of one cell of the EMIF02-600FU7. In this model, the clamping diodes (Dzin and Dzout) are defined by the following PSpice parameters :

$$RS = 0.55$$

$$Cjo = 100p$$

$$M = 0.3333$$

$$VJ = 0.6$$

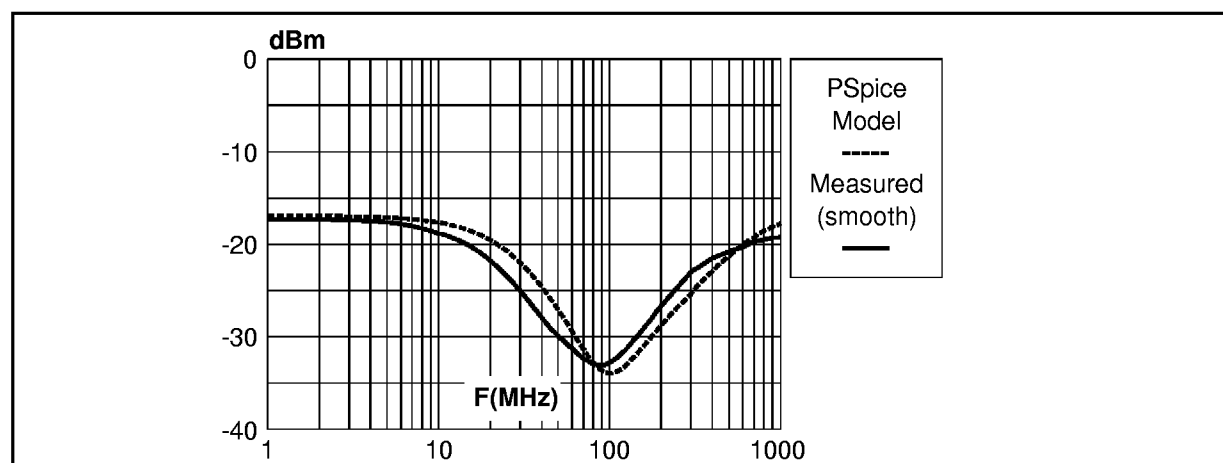
$$BV = 7$$

$$IBV = 1u$$

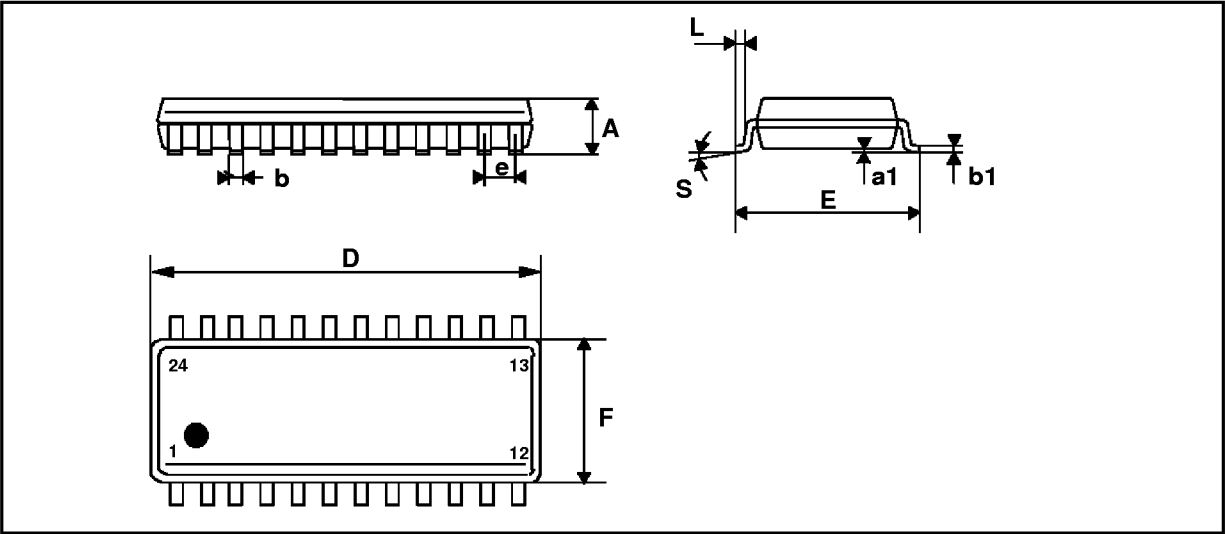
This model is available for frequency simulation and for ambient temperature of 27°C.

The comparison between the PSpice simulation and the measured frequency response is given in figA13. This shows that the PSpice model is very close to the product behavior.

**Fig A13 :** Comparison between PSpice simulation and measured frequency response



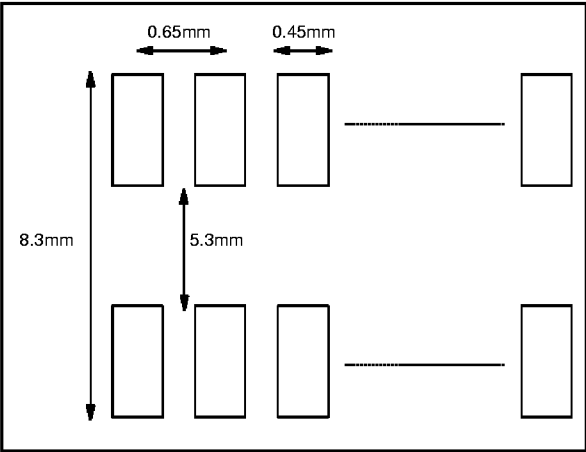
PACKAGE MECHANICAL DATA  
SSOP24



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.73	1.86	2.00	0.068	0.073	0.079
a1	0.05		0.25	0.002		0.010
b	0.25		0.35	0.010		0.014
b1	0.10		0.35	0.0035		0.014
D	8.07	8.20	8.33	0.317	0.322	0.328
E	7.60		7.90	0.299		0.311
e		0.65			0.0256	
F	5.20		5.38	0.2047		0.2118
L	0.25		0.88	0.010		0.0347
S	8° max					

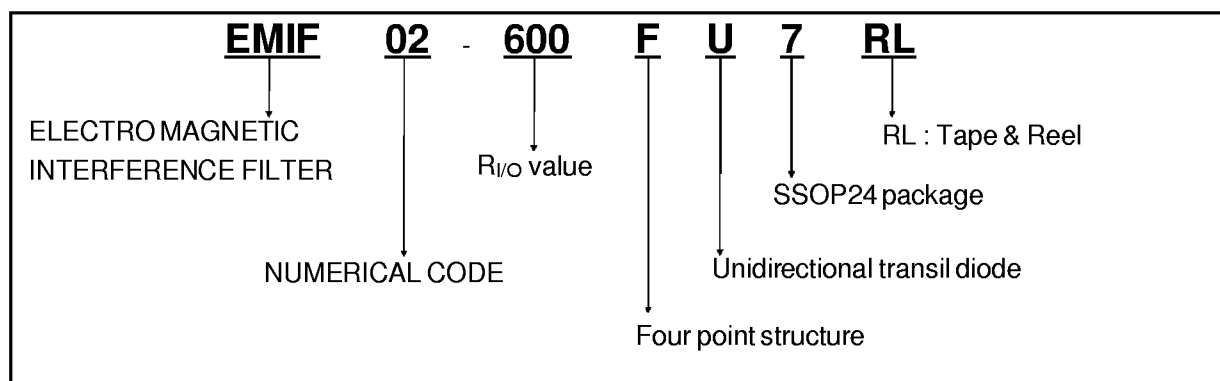
Mechanical specifications	
Lead plating	Tin-lead
Lead plating thickness	7µm min. 20 µm max.
Lead material	Copper alloy
Lead coplanarity	0.08mm max.
Body material	Molded epoxy
Flammability	UL94V-0

RECOMMENDED FOOTPRINT





## ORDER CODE



Order code	Marking	Package	Weight	Base qty	Delivery mode
EMIF02-600FU7	EMIF02-600	SSOP24	0.19g	59	tube
EMIF02-600FU7RL	EMIF02-600	SSOP24	0.19g	2000	tape & reel

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